

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	181	BRASK-JUSTIN-K-.in. BRASK-J-K-.in. BRASK-J-.in. BLOCK-BRUCE-.in. BLOCK-BRUCE-A-.in. BLOCK-B-A-.in. SHAH-U-.in. SHAH-UDAY-.in. SHAH-UDAY-J-.in. SHAH-U-J-.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:37
S2	102	BRASK-JUSTIN-K-.in. BRASK-J-K-.in. BRASK-J-.in. BLOCK-BRUCE-.in. BLOCK-BRUCE-A-.in. BLOCK-B-A-.in. SHAH-U-.in. SHAH-UDAY-.in. SHAH-UDAY-J-.in. SHAH-U-J-.in.	US-PGPUB; USPAT	OR	ON	2005/07/13 16:33
S6	25326	photodector photo-detector photo adj detector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:47
S7	4	S1 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:47
S8	728761	ge germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:47
S9	68835	gallium adj arsenide aluminum adj nitride indium adj intiminide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:13
S10	783858	S8 S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:49
S12	327834	(semiconducting semiconductor semiconductive semi-conducting semi-conductor semi-conductive semi adj conducting semi adj conductor semi adj conductive) near2 (layer film coating material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:51
S13	283800	nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:50

S14	1425145	oxide oxynitride oxy-nitride oxy adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:51
S15	810215	(insulator insulative insulating dielectric) near2 (layer film coating material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:51
S16	819198	resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:52
S17	83	S8 with S13 with S16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:53
S18	24101030	@ad<"20030626"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:08
S25	21041	etch\$3 with (S13 S14 S15) with (barrier protect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:36
S26	1716	etch\$3 with (S13 S14 S15) with (barrier protect\$3) with thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:04
S27	33	S26 same (S10 S12) same S16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:04
S42	126853	S16 near3 (strip\$4 remov\$3 clean\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:34
S43	4	S40 near3 S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:34

S44	47	(S8) near3 (S13 S14 S15) near3 (protect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:35
S45	2	S42 same S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:35
S46	322	(S10 S12) with S42 with (barrier protect\$3 buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:37
S47	161	(S10 S12) with S42 with (barrier protect\$3 buffer) with etch\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:47
S48	140	S18 and S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:46
S49	10	(S8) with S42 with (barrier protect\$3 buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:00
S50	1	(S8) with S42 with (damage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:52
S51	28	(S8) same S42 same (damage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 17:52
S52	2504	etch\$5 near3 (barrier protect\$3 buffer) near2 (thick thickness thin\$4 portion partial\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:18
S53	0	S42 with S52 with damage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:02

S54	90	S42 with S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:16
S58	1962	etch\$5 near3 (thick thickness) near3 (portion partial\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:28
S59	19	S58 same S42 same (damage protect\$5 buffer\$3 barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:28
S61	702	etch\$5 near3 ((thick thickness) near (portion partial\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:28
S62	65	S61 same (damage protect\$5 buffer\$3 barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:28
S63	59	S18 and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:39
S66	2	S10 near3 ((two-step)( two near step)) near3 etch\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:47
S68	34	S10 near3 protect\$5 near3 etch\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:48
S70	33	S68 and S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:50